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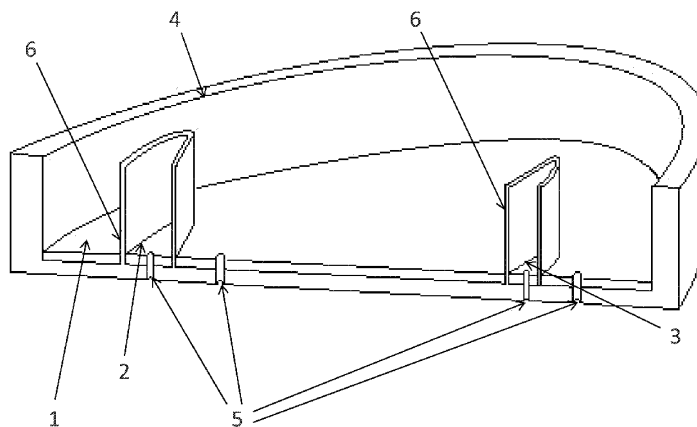


FIG 2

(57) Abstract: The present invention discloses a plating apparatus. The plating apparatus comprises a multiple electrodes. The multiple electrodes include a main electrode and at least two second electrodes. The main electrode and the at least two second electrodes respectively generate an electric field in a corresponding area on the surface of a wafer. The main electrode and the at least two second electrodes respectively have a control interface. By selecting the combination of the control relationship between each second electrode and the main electrode, the wafers with different sizes or different notch shapes are plated, and the control relationship is independent control or joint control. The plating apparatus of the present invention can plate wafers with different sizes or different notch shapes without replacing the whole plating chamber.

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